

74AUP2G132

Low-power dual 2-input NAND Schmitt trigger

Rev. 02 — 14 March 2008

Product data sheet

1. General description

The 74AUP2G132 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

The 74AUP2G132 provides the dual 2-input NAND Schmitt trigger function which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H .

2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu\text{A}$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot $< 10\%$ of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from $-40\text{ }^\circ\text{C}$ to $+85\text{ }^\circ\text{C}$ and $-40\text{ }^\circ\text{C}$ to $+125\text{ }^\circ\text{C}$

3. Applications

- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator

4. Ordering information

Table 1. Ordering information

| Type number | Package | | | Version |
|--------------|-------------------|--------|--|----------|
| | Temperature range | Name | Description | |
| 74AUP2G132DC | -40 °C to +125 °C | VSSOP8 | plastic very thin shrink small outline package; 8 leads; body width 2.3 mm | SOT765-1 |
| 74AUP2G132GT | -40 °C to +125 °C | XSON8 | plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm | SOT833-1 |
| 74AUP2G132GM | -40 °C to +125 °C | XQFN8U | plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm | SOT902-1 |

5. Marking

Table 2. Marking codes

| Type number | Marking code |
|--------------|--------------|
| 74AUP2G132DC | aE2 |
| 74AUP2G132GT | aE2 |
| 74AUP2G132GM | aE2 |

6. Functional diagram

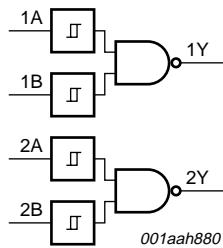


Fig 1. Logic symbol

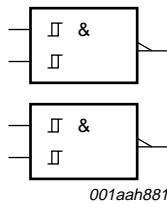


Fig 2. IEC logic symbol

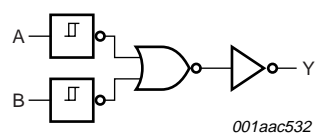


Fig 3. Logic diagram (one gate)

7. Pinning information

7.1 Pinning

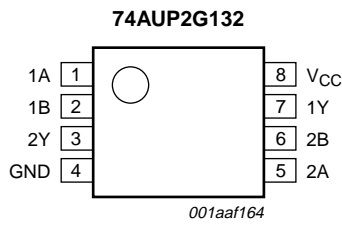


Fig 4. Pin configuration SOT765-1 (VSSOP8)

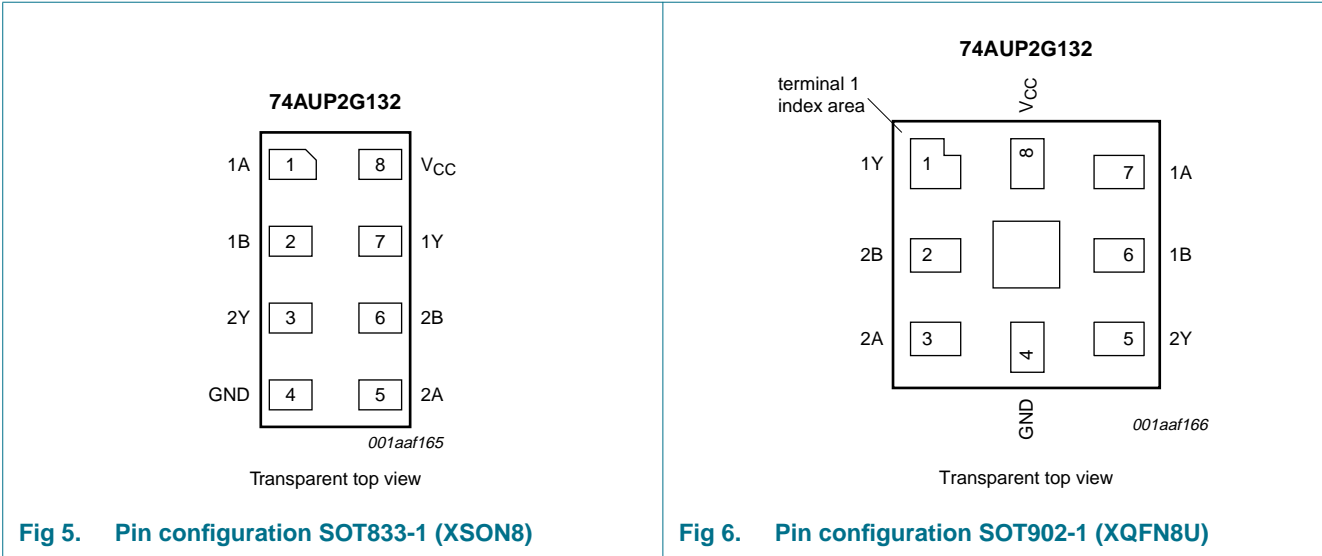


Fig 5. Pin configuration SOT833-1 (XSON8)

Fig 6. Pin configuration SOT902-1 (XQFN8U)

7.2 Pin description

Table 3. Pin description

| Symbol | Pin | | Description |
|-----------------|-----------------------|----------|----------------|
| | SOT765-1 and SOT833-1 | SOT902-1 | |
| 1A | 1 | 7 | data input 1A |
| 1B | 2 | 6 | data input 1B |
| 2Y | 3 | 5 | data output 2Y |
| GND | 4 | 4 | ground (0 V) |
| 2A | 5 | 3 | data input 2A |
| 2B | 6 | 2 | data input 2B |
| 1Y | 7 | 1 | data output 1Y |
| V _{CC} | 8 | 8 | supply voltage |

8. Functional description

Table 4. Function table^[1]

| Input | | Output |
|-------|----|--------|
| nA | nB | nY |
| L | L | H |
| L | H | H |
| H | L | H |
| H | H | L |

[1] H = HIGH voltage level;
L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|---------------------------------|----------|----------|------|
| V_{CC} | supply voltage | | -0.5 | +4.6 | V |
| I_{IK} | input clamping current | $V_I < 0$ V | - | -50 | mA |
| V_I | input voltage | | [1] -0.5 | +4.6 | V |
| I_{OK} | output clamping current | $V_O < 0$ V | - | -50 | mA |
| V_O | output voltage | Active mode and Power-down mode | [1] -0.5 | +4.6 | V |
| I_O | output current | $V_O = 0$ V to V_{CC} | - | ± 20 | mA |
| I_{CC} | supply current | | - | 50 | mA |
| I_{GND} | ground current | | - | -50 | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | $T_{amb} = -40$ °C to +125 °C | [2] - | 250 | mW |

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
For XSON8 and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Recommended operating conditions

Table 6. Operating conditions

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|---------------------|---------------------------------|-----|----------|------|
| V_{CC} | supply voltage | | 0.8 | 3.6 | V |
| V_I | input voltage | | 0 | 3.6 | V |
| V_O | output voltage | Active mode | 0 | V_{CC} | V |
| | | Power-down mode; $V_{CC} = 0$ V | 0 | 3.6 | V |
| T_{amb} | ambient temperature | | -40 | +125 | °C |

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|--------------------------------------|--|------------------------|-----|-----------------------|------|
| T_{amb} = 25 °C | | | | | | |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V | V _{CC} - 0.1 | - | - | V |
| | | I _O = -1.1 mA; V _{CC} = 1.1 V | 0.75 × V _{CC} | - | - | V |
| | | I _O = -1.7 mA; V _{CC} = 1.4 V | 1.11 | - | - | V |
| | | I _O = -1.9 mA; V _{CC} = 1.65 V | 1.32 | - | - | V |
| | | I _O = -2.3 mA; V _{CC} = 2.3 V | 2.05 | - | - | V |
| | | I _O = -3.1 mA; V _{CC} = 2.3 V | 1.9 | - | - | V |
| | | I _O = -2.7 mA; V _{CC} = 3.0 V | 2.72 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.6 | - | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V | - | - | 0.1 | V |
| | | I _O = 1.1 mA; V _{CC} = 1.1 V | - | - | 0.3 × V _{CC} | V |
| | | I _O = 1.7 mA; V _{CC} = 1.4 V | - | - | 0.31 | V |
| | | I _O = 1.9 mA; V _{CC} = 1.65 V | - | - | 0.31 | V |
| | | I _O = 2.3 mA; V _{CC} = 2.3 V | - | - | 0.31 | V |
| | | I _O = 3.1 mA; V _{CC} = 2.3 V | - | - | 0.44 | V |
| | | I _O = 2.7 mA; V _{CC} = 3.0 V | - | - | 0.31 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.44 | V |
| I _I | input leakage current | V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V | - | - | ±0.1 | μA |
| I _{OFF} | power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V | - | - | ±0.2 | μA |
| ΔI _{OFF} | additional power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V | - | - | ±0.2 | μA |
| I _{CC} | supply current | V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V | - | - | 0.5 | μA |
| ΔI _{CC} | additional supply current | V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V | 1 - | - | 40 | μA |
| C _I | input capacitance | V _I = GND or V _{CC} ; V _{CC} = 0 V to 3.6 V | - | 1.1 | - | pF |
| C _O | output capacitance | V _O = GND; V _{CC} = 0 V | - | 1.7 | - | pF |
| T_{amb} = -40 °C to +85 °C | | | | | | |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V | V _{CC} - 0.1 | - | - | V |
| | | I _O = -1.1 mA; V _{CC} = 1.1 V | 0.7 × V _{CC} | - | - | V |
| | | I _O = -1.7 mA; V _{CC} = 1.4 V | 1.03 | - | - | V |
| | | I _O = -1.9 mA; V _{CC} = 1.65 V | 1.30 | - | - | V |
| | | I _O = -2.3 mA; V _{CC} = 2.3 V | 1.97 | - | - | V |
| | | I _O = -3.1 mA; V _{CC} = 2.3 V | 1.85 | - | - | V |
| | | I _O = -2.7 mA; V _{CC} = 3.0 V | 2.67 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.55 | - | - | V |

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------|--------------------------------------|--|-----|-----|-----------------------|------|
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V | - | - | 0.1 | V |
| | | I _O = 1.1 mA; V _{CC} = 1.1 V | - | - | 0.3 × V _{CC} | V |
| | | I _O = 1.7 mA; V _{CC} = 1.4 V | - | - | 0.37 | V |
| | | I _O = 1.9 mA; V _{CC} = 1.65 V | - | - | 0.35 | V |
| | | I _O = 2.3 mA; V _{CC} = 2.3 V | - | - | 0.33 | V |
| | | I _O = 3.1 mA; V _{CC} = 2.3 V | - | - | 0.45 | V |
| | | I _O = 2.7 mA; V _{CC} = 3.0 V | - | - | 0.33 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.45 | V |
| I _I | input leakage current | V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V | - | - | ±0.5 | μA |
| I _{OFF} | power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V | - | - | ±0.5 | μA |
| ΔI _{OFF} | additional power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V | - | - | ±0.6 | μA |
| I _{CC} | supply current | V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V | - | - | 0.9 | μA |
| ΔI _{CC} | additional supply current | V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V | [1] | - | 50 | μA |

T_{amb} = -40 °C to +125 °C

| | | | | | | |
|------------------|---------------------------|--|------------------------|---|------------------------|----|
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V | V _{CC} - 0.11 | - | - | V |
| | | I _O = -1.1 mA; V _{CC} = 1.1 V | 0.6 × V _{CC} | - | - | V |
| | | I _O = -1.7 mA; V _{CC} = 1.4 V | 0.93 | - | - | V |
| | | I _O = -1.9 mA; V _{CC} = 1.65 V | 1.17 | - | - | V |
| | | I _O = -2.3 mA; V _{CC} = 2.3 V | 1.77 | - | - | V |
| | | I _O = -3.1 mA; V _{CC} = 2.3 V | 1.67 | - | - | V |
| | | I _O = -2.7 mA; V _{CC} = 3.0 V | 2.40 | - | - | V |
| | | I _O = -4.0 mA; V _{CC} = 3.0 V | 2.30 | - | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | |
| | | I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V | - | - | 0.11 | V |
| | | I _O = 1.1 mA; V _{CC} = 1.1 V | - | - | 0.33 × V _{CC} | V |
| | | I _O = 1.7 mA; V _{CC} = 1.4 V | - | - | 0.41 | V |
| | | I _O = 1.9 mA; V _{CC} = 1.65 V | - | - | 0.39 | V |
| | | I _O = 2.3 mA; V _{CC} = 2.3 V | - | - | 0.36 | V |
| | | I _O = 3.1 mA; V _{CC} = 2.3 V | - | - | 0.50 | V |
| | | I _O = 2.7 mA; V _{CC} = 3.0 V | - | - | 0.36 | V |
| | | I _O = 4.0 mA; V _{CC} = 3.0 V | - | - | 0.50 | V |
| I _I | input leakage current | V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V | - | - | ±0.75 | μA |
| I _{OFF} | power-off leakage current | V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V | - | - | ±0.75 | μA |

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|--------------------------------------|---|-----|-----|------------|---------|
| ΔI_{OFF} | additional power-off leakage current | V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V | - | - | ± 0.75 | μ A |
| I_{CC} | supply current | $V_I = GND$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V | - | - | 1.4 | μ A |
| ΔI_{CC} | additional supply current | $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V | [1] | - | 75 | μ A |

[1] One input at $V_{CC} - 0.6$ V, other input at V_{CC} or GND.

12. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#)).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +125 °C | | | Unit |
|--------|-----------|------------|-------|--------------------|-----|-------------------|-------------|--------------|------|
| | | | Min | Typ ^[1] | Max | Min | Max (85 °C) | Max (125 °C) | |

$C_L = 5$ pF

| | | | | | | | | | |
|----------|-------------------|--|-----|------|------|-----|------|------|----|
| t_{pd} | propagation delay | nA or nB to nY; see Figure 7 [2] | | | | | | | |
| | | $V_{CC} = 0.8$ V | - | 22.5 | - | - | - | - | ns |
| | | $V_{CC} = 1.1$ V to 1.3 V | 2.6 | 6.3 | 13.4 | 2.4 | 15.1 | 16.6 | ns |
| | | $V_{CC} = 1.4$ V to 1.6 V | 2.2 | 4.6 | 8.2 | 1.9 | 9.7 | 10.7 | ns |
| | | $V_{CC} = 1.65$ V to 1.95 V | 1.9 | 3.9 | 6.6 | 1.7 | 7.9 | 8.7 | ns |
| | | $V_{CC} = 2.3$ V to 2.7 V | 1.7 | 3.2 | 5.3 | 1.5 | 6.2 | 6.8 | ns |
| | | $V_{CC} = 3.0$ V to 3.6 V | 1.6 | 2.9 | 4.7 | 1.4 | 5.6 | 6.2 | ns |

$C_L = 10$ pF

| | | | | | | | | | |
|----------|-------------------|--|-----|------|------|-----|------|------|----|
| t_{pd} | propagation delay | nA or nB to nY; see Figure 7 [2] | | | | | | | |
| | | $V_{CC} = 0.8$ V | - | 26.1 | - | - | - | - | ns |
| | | $V_{CC} = 1.1$ V to 1.3 V | 3.0 | 7.2 | 15.4 | 2.7 | 17.3 | 19.0 | ns |
| | | $V_{CC} = 1.4$ V to 1.6 V | 2.5 | 5.2 | 9.3 | 2.2 | 11.0 | 12.1 | ns |
| | | $V_{CC} = 1.65$ V to 1.95 V | 2.3 | 4.5 | 7.5 | 2.0 | 9.0 | 9.9 | ns |
| | | $V_{CC} = 2.3$ V to 2.7 V | 2.1 | 3.8 | 6.1 | 1.8 | 7.2 | 7.9 | ns |
| | | $V_{CC} = 3.0$ V to 3.6 V | 2.0 | 3.5 | 5.5 | 1.8 | 6.5 | 7.2 | ns |

$C_L = 15$ pF

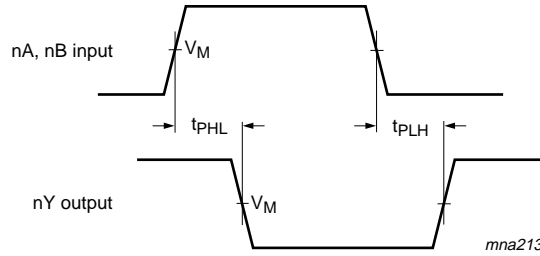
| | | | | | | | | | |
|----------|-------------------|--|-----|------|------|-----|------|------|----|
| t_{pd} | propagation delay | nA or nB to nY; see Figure 7 [2] | | | | | | | |
| | | $V_{CC} = 0.8$ V | - | 29.6 | - | - | - | - | ns |
| | | $V_{CC} = 1.1$ V to 1.3 V | 3.3 | 8.0 | 17.2 | 3.0 | 19.4 | 21.3 | ns |
| | | $V_{CC} = 1.4$ V to 1.6 V | 2.8 | 5.8 | 10.4 | 2.5 | 12.3 | 13.5 | ns |
| | | $V_{CC} = 1.65$ V to 1.95 V | 2.6 | 5.0 | 8.3 | 2.3 | 10.0 | 11.0 | ns |
| | | $V_{CC} = 2.3$ V to 2.7 V | 2.3 | 4.2 | 6.7 | 2.1 | 7.9 | 8.7 | ns |
| | | $V_{CC} = 3.0$ V to 3.6 V | 2.2 | 3.9 | 6.1 | 2.0 | 7.3 | 8.0 | ns |

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +125 °C | | | Unit |
|---|-------------------------------|--|-------|--------------------|------|-------------------|-------------|--------------|------|
| | | | Min | Typ ^[1] | Max | Min | Max (85 °C) | Max (125 °C) | |
| C_L = 30 pF | | | | | | | | | |
| t _{pd} | propagation delay | nA or nB to nY; see Figure 7 ^[2] | | | | | | | |
| | | V _{CC} = 0.8 V | - | 39.9 | - | - | - | - | ns |
| | | V _{CC} = 1.1 V to 1.3 V | 4.3 | 10.2 | 22.6 | 3.8 | 25.4 | 27.9 | ns |
| | | V _{CC} = 1.4 V to 1.6 V | 3.6 | 7.3 | 13.3 | 3.2 | 15.8 | 17.4 | ns |
| | | V _{CC} = 1.65 V to 1.95 V | 3.2 | 6.3 | 10.6 | 2.9 | 12.8 | 14.1 | ns |
| | | V _{CC} = 2.3 V to 2.7 V | 3.0 | 5.3 | 8.5 | 2.7 | 10.1 | 11.1 | ns |
| | | V _{CC} = 3.0 V to 3.6 V | 2.8 | 5.0 | 7.8 | 2.7 | 9.2 | 10.1 | ns |
| C_L = 5 pF, 10 pF, 15 pF and 30 pF | | | | | | | | | |
| C _{PD} | power dissipation capacitance | f _i = 1 MHz; V _I = GND to V _{CC} ^[3] | | | | | | | |
| | | V _{CC} = 0.8 V | - | 2.6 | - | - | - | - | pF |
| | | V _{CC} = 1.1 V to 1.3 V | - | 2.9 | - | - | - | - | pF |
| | | V _{CC} = 1.4 V to 1.6 V | - | 3.0 | - | - | - | - | pF |
| | | V _{CC} = 1.65 V to 1.95 V | - | 3.2 | - | - | - | - | pF |
| | | V _{CC} = 2.3 V to 2.7 V | - | 3.8 | - | - | - | - | pF |
| | | V _{CC} = 3.0 V to 3.6 V | - | 4.4 | - | - | - | - | pF |

[1] All typical values are measured at nominal V_{CC}.
 [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

13. Waveforms

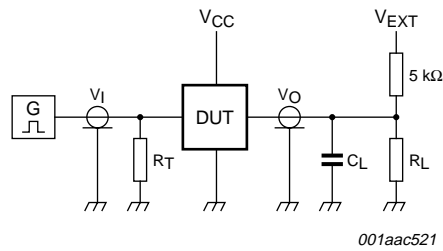


Measurement points are given in [Table 9](#).
 Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 7. The data input (nA or nB) to output (nY) propagation delays

Table 9. Measurement points

| Supply voltage | Output | Input | | |
|----------------|---------------------|---------------------|----------|---------------|
| V_{CC} | V_M | V_M | V_I | $t_r = t_f$ |
| 0.8 V to 3.6 V | $0.5 \times V_{CC}$ | $0.5 \times V_{CC}$ | V_{CC} | ≤ 3.0 ns |



Test data is given in [Table 10](#).
 Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuitry for switching times

Table 10. Test data

| Supply voltage | Load | | V_{EXT} | | |
|----------------|------------------------------|--------------|--------------------|--------------------|--------------------|
| V_{CC} | C_L | R_L [1] | t_{PLH}, t_{PHL} | t_{PZH}, t_{PHZ} | t_{PZL}, t_{PLZ} |
| 0.8 V to 3.6 V | 5 pF, 10 pF, 15 pF and 30 pF | 5 kΩ or 1 MΩ | open | GND | $2 \times V_{CC}$ |

[1] For measuring enable and disable times $R_L = 5$ kΩ, for measuring propagation delays, setup and hold times and pulse width $R_L = 1$ MΩ.

14. Transfer characteristics

Table 11. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#).)

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +125 °C | | | Unit |
|-----------------|---|--|-------|-----|------|-------------------|-------------|--------------|------|
| | | | Min | Typ | Max | Min | Max (85 °C) | Max (125 °C) | |
| V _{T+} | positive-going threshold voltage | see Figure 9 and Figure 10 | | | | | | | |
| | | V _{CC} = 0.8 V | 0.30 | - | 0.60 | 0.30 | 0.60 | 0.62 | V |
| | | V _{CC} = 1.1 V | 0.53 | - | 0.90 | 0.53 | 0.90 | 0.92 | V |
| | | V _{CC} = 1.4 V | 0.74 | - | 1.11 | 0.74 | 1.11 | 1.13 | V |
| | | V _{CC} = 1.65 V | 0.91 | - | 1.29 | 0.91 | 1.29 | 1.31 | V |
| | | V _{CC} = 2.3 V | 1.37 | - | 1.77 | 1.37 | 1.77 | 1.80 | V |
| | | V _{CC} = 3.0 V | 1.88 | - | 2.29 | 1.88 | 2.29 | 2.32 | V |
| V _{T-} | negative-going threshold voltage | see Figure 9 and Figure 10 | | | | | | | |
| | | V _{CC} = 0.8 V | 0.10 | - | 0.60 | 0.10 | 0.60 | 0.60 | V |
| | | V _{CC} = 1.1 V | 0.26 | - | 0.65 | 0.26 | 0.65 | 0.65 | V |
| | | V _{CC} = 1.4 V | 0.39 | - | 0.75 | 0.39 | 0.75 | 0.75 | V |
| | | V _{CC} = 1.65 V | 0.47 | - | 0.84 | 0.47 | 0.84 | 0.84 | V |
| | | V _{CC} = 2.3 V | 0.69 | - | 1.04 | 0.69 | 1.04 | 1.04 | V |
| | | V _{CC} = 3.0 V | 0.88 | - | 1.24 | 0.88 | 1.24 | 1.24 | V |
| V _H | hysteresis voltage (V _{T+} - V _{T-}); see Figure 9 , Figure 10 , Figure 11 and Figure 12 | | | | | | | | |
| | | V _{CC} = 0.8 V | 0.07 | - | 0.50 | 0.07 | 0.50 | 0.50 | V |
| | | V _{CC} = 1.1 V | 0.08 | - | 0.46 | 0.08 | 0.46 | 0.46 | V |
| | | V _{CC} = 1.4 V | 0.18 | - | 0.56 | 0.18 | 0.56 | 0.56 | V |
| | | V _{CC} = 1.65 V | 0.27 | - | 0.66 | 0.27 | 0.66 | 0.66 | V |
| | | V _{CC} = 2.3 V | 0.53 | - | 0.92 | 0.53 | 0.92 | 0.92 | V |
| | | V _{CC} = 3.0 V | 0.79 | - | 1.31 | 0.79 | 1.31 | 1.31 | V |

15. Waveforms transfer characteristics

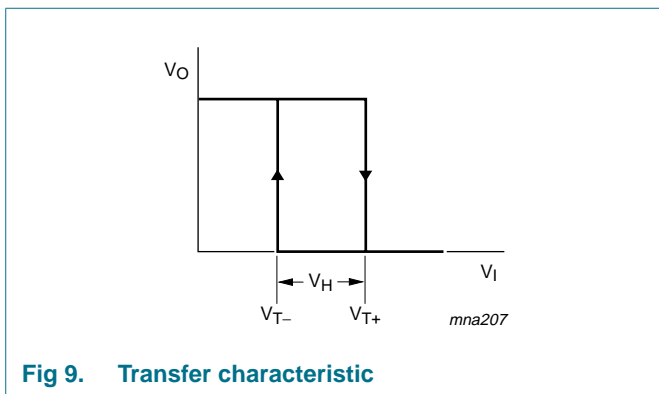


Fig 9. Transfer characteristic

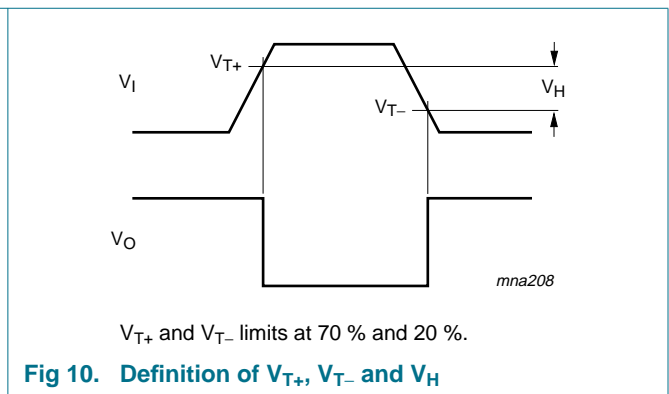
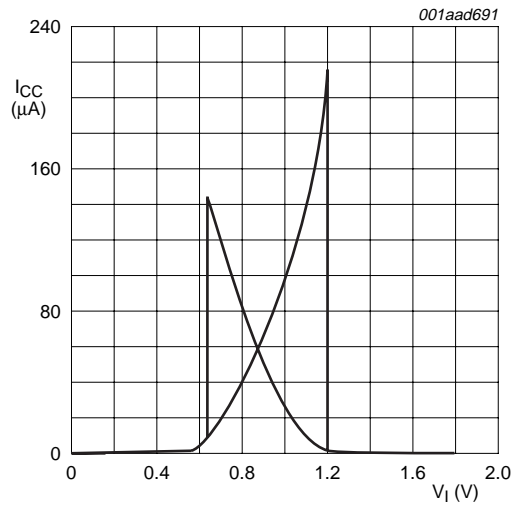
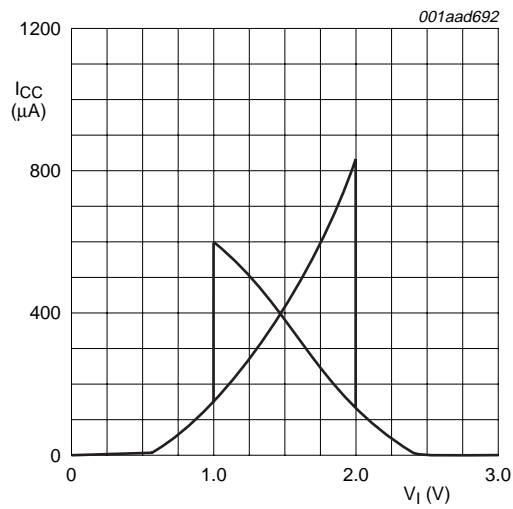


Fig 10. Definition of V_{T+}, V_{T-} and V_H



$V_{CC} = 3.0$ V.

Fig 11. Typical transfer characteristics; $V_{CC} = 1.8$ V



$V_{CC} = 3.0$ V.

Fig 12. Typical transfer characteristics; $V_{CC} = 3.0$ V

16. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

$$P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$$

P_{add} = additional power dissipation (μW);

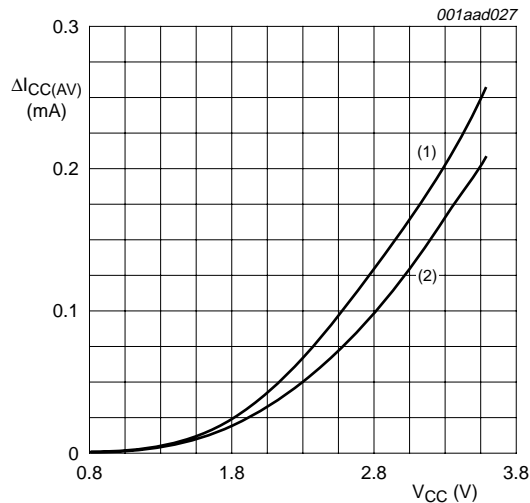
f_i = input frequency (MHz);

t_r = input rise time (ns); 10 % to 90 %;

t_f = input fall time (ns); 90 % to 10 %;

$\Delta I_{CC(AV)}$ = average additional supply current (μA).

Average $\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in [Figure 13](#).



- (1) Positive-going edge.
- (2) Negative-going edge.

Linear change of V_I between 0.8 V and 2.0 V. All values given are typical, unless otherwise specified.

Fig 13. Average I_{CC} as a function of V_{CC}

17. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

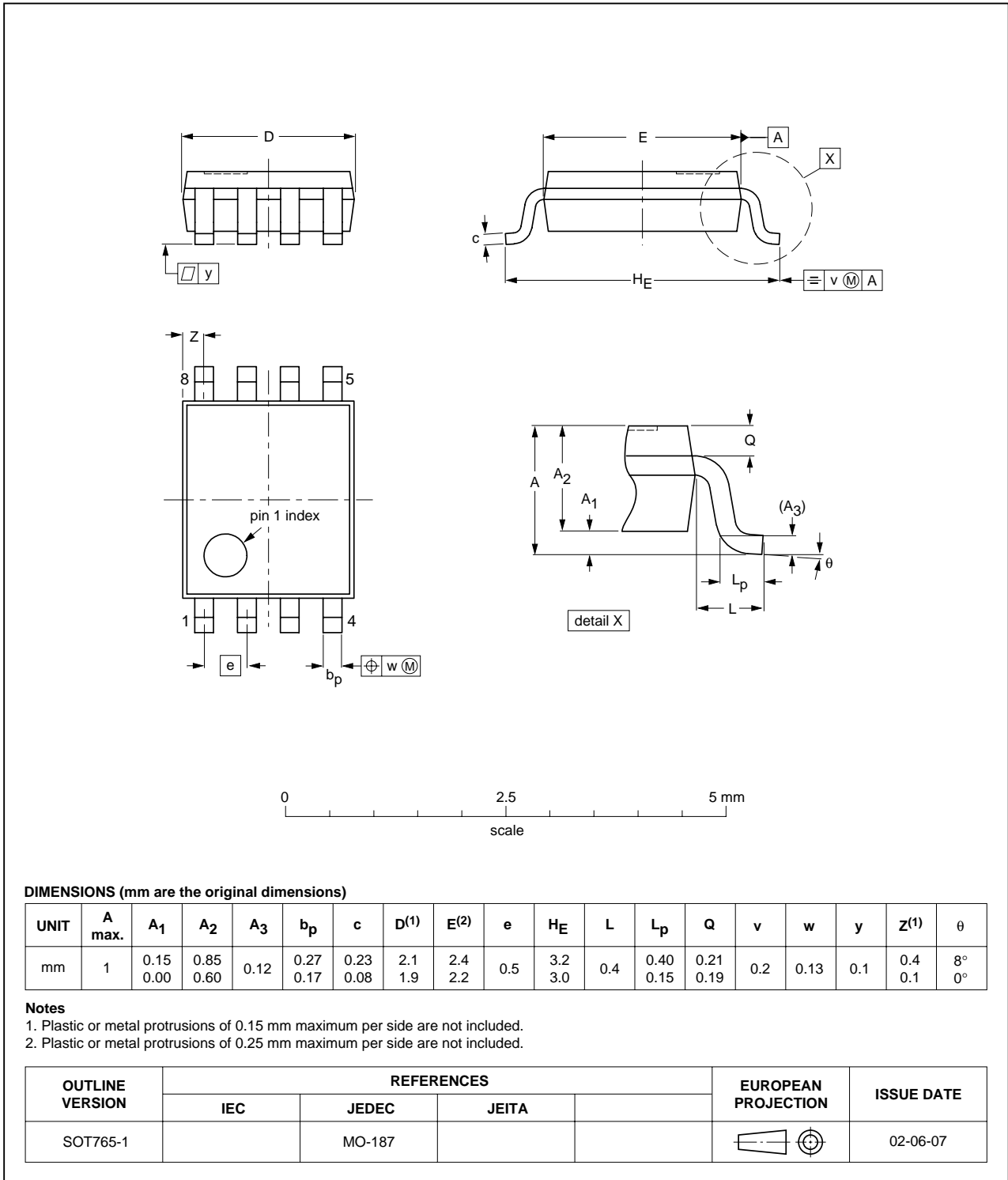


Fig 14. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

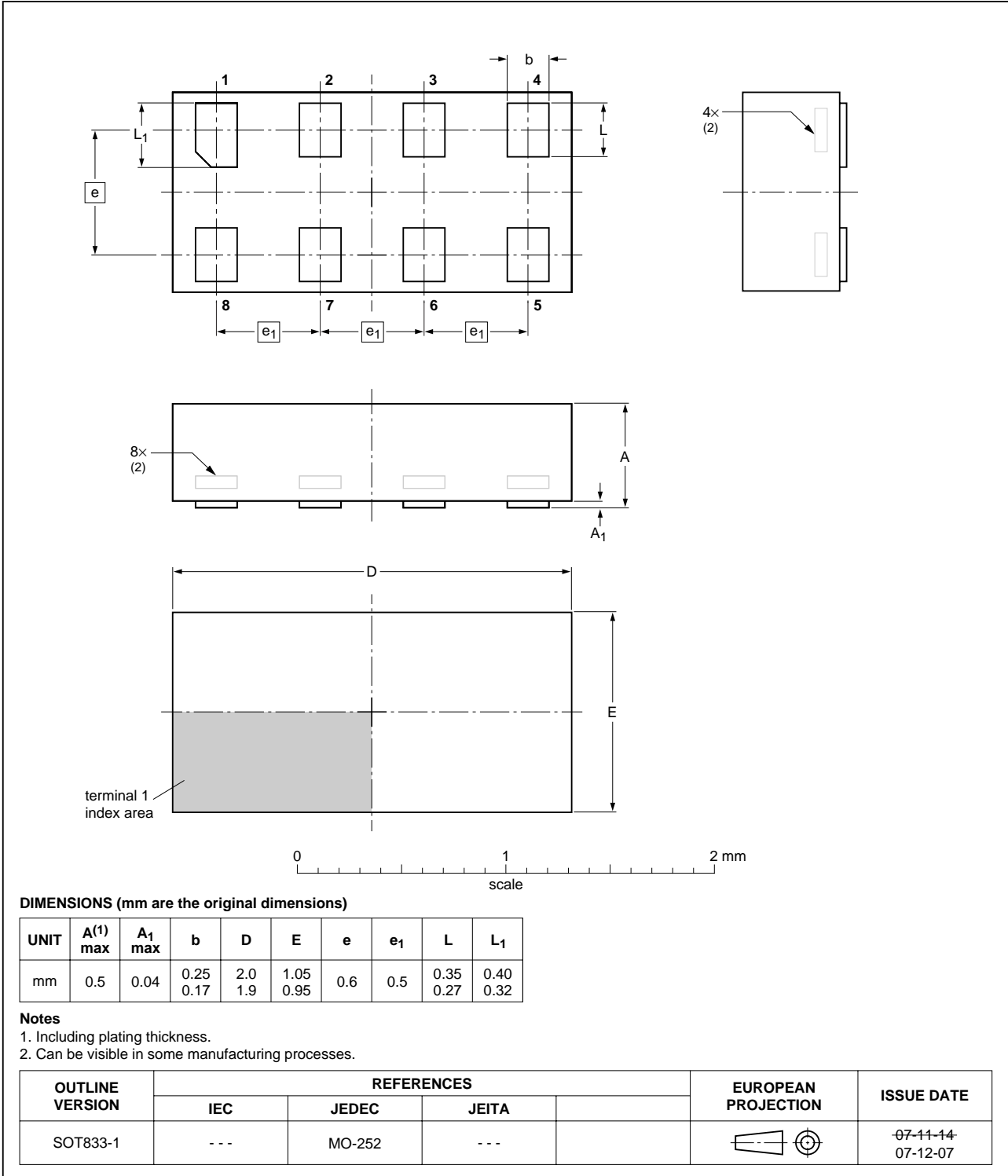


Fig 15. Package outline SOT833-1 (XSON8)

XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1

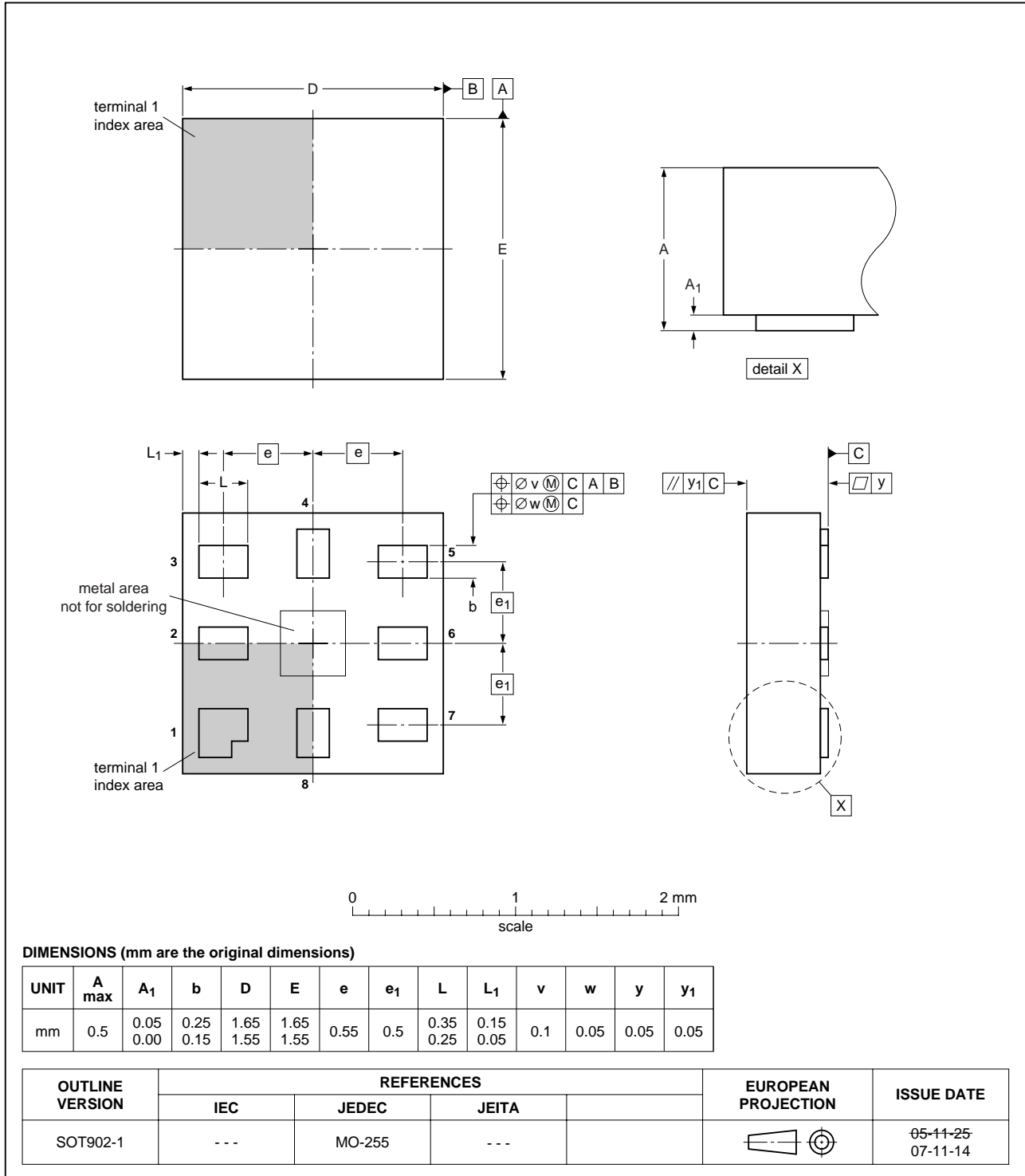


Fig 16. Package outline SOT902-1 (XQFN8U)

18. Abbreviations

Table 12. Abbreviations

| Acronym | Description |
|---------|---|
| CDM | Charged Device Model |
| CMOS | Complementary Metal-Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |
| TTL | Transistor-Transistor Logic |

19. Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--|---------------|--------------|
| 74AUP2G132_2 | 20080314 | Product data sheet | - | 74AUP2G132_1 |
| Modifications: | | <ul style="list-style-type: none">• Figure 1 and Figure 2: pin numbers removed from logic symbols• Figure 16: package outline drawing updated to latest version | | |
| 74AUP2G132_1 | 20061018 | Product data sheet | - | - |

20. Legal information

20.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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22. Contents

1 **General description** 1

2 **Features** 1

3 **Applications** 1

4 **Ordering information** 2

5 **Marking** 2

6 **Functional diagram** 2

7 **Pinning information** 2

7.1 Pinning 2

7.2 Pin description 3

8 **Functional description** 3

9 **Limiting values** 4

10 **Recommended operating conditions** 4

11 **Static characteristics** 5

12 **Dynamic characteristics** 7

13 **Waveforms** 9

14 **Transfer characteristics** 10

15 **Waveforms transfer characteristics** 10

16 **Application information** 12

17 **Package outline** 13

18 **Abbreviations** 16

19 **Revision history** 16

20 **Legal information** 17

20.1 Data sheet status 17

20.2 Definitions 17

20.3 Disclaimers 17

20.4 Trademarks 17

21 **Contact information** 17

22 **Contents** 18

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